PCN Num	her		2017	<u>0424</u>	1002			PCN I	Date:	Δnr	il 25, 2017
Qualification of add											
Title: Qualification of additional Fab site (RFAB) and Assembly site (ASEN) option for select devices											
Customer Contact:			PCN Manager				Dept:			ality Services	
Proposed 1 st Ship Date:						Estimat			Date provided at		
Proposed	1 1 Sn	ip Date:	•	July 2	25, 2017		Availab	ility:	-	san	nple request.
Change T	уре:										
	mbly Sit	te			Assembly Pr	ocess		Assembly Materials		Materials	
Desig					Electrical Sp			Mechanical Specificati			
☐ Test					Packing/Ship						
	r Bump				Wafer Bump			Wafer Bump Process			
	r Fab S	ite		= -	Wafer Fab M			Wafer Fab Process			
					Part number						
					PCN	<u>Deta</u>	IIS				
Descripti	on of C	hange:									
	(ASEN)		he se	lecte	ounce the qu d devices lis		"Product	Affec		ion.	
Current	Fab	Proce			Wafer	Add	litional		Process		Wafer
Site		11000	.55	D	Diameter		b Site		100033		Diameter
DP1D		LBC	7	_	200 mm		RFAB		LBC7		300 mm
Test coverage, insertions, contest MQ.			mpou	ınd	SID#CZ0	0140			002614	J	d verified with
Reason fo	or Cha	nge:									
Continuity											
Anticipat	ed imp	act on F	orm,	Fit,	Function, Q	uality	or Reli	abilit	y (positi	ive /	negative):
None			•	•							
Anticipat	ed imp	act on M	later	ial D	eclaration						
No Impact to the Material Declaration			Material Declarations or Product Content reports are driven from production data and will be available following the production release. Upon production release the revised reports can be obtained from the TI ECO website.								
Changes to product identification resulting from this PCN:											
	-										
Fab Site				hip S	Site Origin	1			<u> </u>		
Chip Site			Code (20L)		Chi	Chip Site Country Code (2		Code (21	1L)	Chip Site City	
DP1DM5			DM5			USA			Dallas		
	RFAB				RFB			USA			Richardson

Assembly Site Information:

Assembly Site Assembly Site Origin (22L)		Assembly Country Code (21L)	Assembly City	
UTAC	NSE	THA	Bangkok	
ASEN	ASN	CHN	Suzhou	

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 20:

MSL 2 /260C/1 YEAR SEAL DT

MSL 1 /235C/UNLIM 03/29/04

(1P) SN74LS07NSR (D) 0336 31T)LOT: 3959047MLA 4W) TKY(1T) 7523483S12 (P) (2P (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MV

ACO - MYS

OPT: ITEM:

(L)T0:³9750

Topside Device marking (if included):

Assembly site code for NSE= P Assembly site code for ASN = W

Product Affected:

Group 1 device list - Qualify both RFAB and ASEN

TS3USB3000MRSER TS3USB3000RSER

Group 2 device list - Qualify only RFAB (ASEN already qualified)

TS3USB3000AMRSER

Qualification Report

TS3USB3000RSER, TS3USB3000MRSE and TS3USB3000AMRSE

Approve Date 13-Apr-2017

Product Attributes

Attributes	Qual Device: TS3USB3000RSER	QBS Product Reference: TPS51225C	QBS Product Reference: TS3U SB3000R SER	QBS Product Reference: TS3USB3000RSER	QBS Process Reference: ALM2402QDRRRQ1
Wafer Fab Supplier	RFAB	RFAB	MIHO8	DP1-DM5	RFAB
Wafer Process	LBC7	LBC7	LBC7	LBC7	LBC7
Assembly Site	ASEN	CLARK	NSE (UTAC)	ASEN	CLARK
Package Family	QFN	QFN	QFN	QFN	SON

⁻ QBS: Qual By Similarity - Qual Device TS3USB3000RSER is qualified at LEVEL1-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: TS3USB3000RSER	QBS Product Reference: TPS51225C	QBS Product Reference: T \$3U \$B3000R \$ER	QBS Product Reference: T S3U SB3000R SER	QBS Process Reference: ALM2402QDRRRQ1
AC	Autoclave 121C	96 Hours	-	3/231/0	-	3/231/0	3/231/0
ED	Electrical Distributions	Cpk>1.67 Room, hot, and cold test	-	-	-	-	3/90/0
ED	Electrical Characterization	Per Datasheet Parameters	-	Pass	Pass	Pass	-
ELFR	Early Life Failure Rate, 150C	24 Hours	-	-	-	-	1/800/0
HAST	Biased HAST, 130C/85%RH	96 Hours	2/154/0	3/231/0	-	3/231/0	3/231/0
HBM	ESD - HBM	6000 V	1/3/0	-	-	1/3/0	-
CDM	ESD - CDM	1500 V	1/3/0	2/6/0	1/3/0	-	1/3/0
HTOL	Life Test, 125C	1000 Hours	-	3/231/0	-	-	1/77/0
HTOL	Life Test, 150C	300 Hours	-	-	-	1/77/0	2/154/0
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	-	-	3/231/0	-
HTSL	High Temp. Storage Bake, 150C	1000 Hours	-	3/231/0	-	-	1/45/0
LU	Latch-up	(per JESD78)	1/6/0	2/12/0	1/6/0	2/12/0	1/6/0
PD	Physical Dimensions	-	-	-	-	3/30/0	3/30/0
SD	Surface Mount Solderability	Pb-Free	-	-	-	3/69/0	3/45/0
SD	Surface Mount Solderability	Pb	-	-	-	-	3/45/0
TC	Temperature Cycle -65C/150C	500 Cycles	1/77/0	3/231/0	-	3/231/0	3/231/0
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass				
WBP	Bond Pull	Wires	-	-	-	3/90/0	3/228/0
WBS	Ball Bond Shear	Wires	•	-	-	3/15/0	3/90/0
MSL	Moisture Sensitivity	Level 1, 260C	1/12/0				
Preconditio	ning was performed for Autoclave. L	Inbiased HAST, THB/Biased HAST, Tem	perature Cycle, Thermal Shock,	and HTSL, as applicable		•	

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles
Quality and Environmental data is available at TI's external Web site: http://www.ti.com/
Green/Pb-Free Status:
Qualified Pb-Free (SMT) and Green



Qualification Report

TS3USB3000RSER and SAP spins TS3USB3000MRSE and TS3USB3000AMRSE Second Source Offload in ASEN Approve Date 17-Feb-2017

Product Attributes

Die Attributes	Qual Device: TS3USB3000RSER	QBS Process Reference: TPS22932YFP	QBS Process Reference: TPX3110D2PWP
Wafer Fab Supplier	DP1-DM5	DMOS5	MIHO8
Wafer Process	LBC7	3370LBC7	LBC7
Assembly Site	ASEN	SCS	TAI
Package Family	QFN; 2 x1.5MM	WLBGA	TSSOP

⁻ QBS: Qual By Similarity

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: T S3U SB3000R SER	QBS Process Reference: TPS22932YFP	QBS Process Reference: TPX3110D2PWP
AC	Autoclave 121C	96 Hours	3/231/0	-	3/231/0
ED	Electrical Characterization	Per Datasheet Parameters	Pass	Pass	Pass
ELFR	Early Life Failure Rate, 150C	24 Hours	-	-	3/2400/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0	-	3/231/0
HBM	ESD - HBM	6000 V	1/3/0	-	-
CDM	ESD - CDM	1000 V	1/3/0	-	2/6/0
HTOL	Life Test, 150C	300 Hours	1/77/0	1/77/0	3/231/0
HTSL	High Temp Storage Bake 170C	420 Hours	3/231/0	-	3/231/0
LU	Latch-up	(per JESD78)	2/12/0	1/6/0	-
PD	Physical Dimensions	(per mechanical drawing)	3/30/0	-	-
SD	Surface Mount Solderability	Pb Free	3/69/0	-	-
TC	Temperature Cycle, -55/125C	1000 Cycles	-	1/77/0	3/231/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0	-	3/231/0
TS	Thermal Shock -65/150C	500 Cycles	-	-	3/231/0
WBP	Bond Pull	Wires	3/90/0	-	-
WBS	Ball Bond Shear	Wires	3/15/0	-	-

Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com

⁻ Qual Device TS3USB3000RSER is qualified at LEVEL1-260C

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours - The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours

⁻ The following are equivalent Tiss options based on an activation energy of 0.7 eV: 1900 Nr. 1900 Nr.